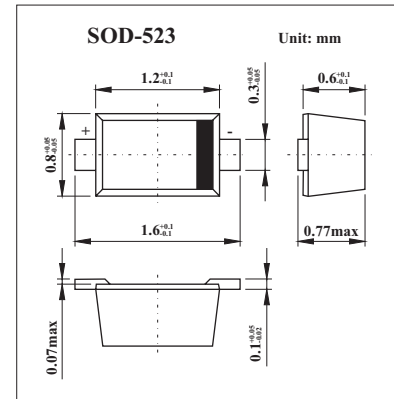


RF PIN Diode

BAR63V-02V

■ Features

- Low forward resistance
- Space saving SOD-523 package with low series inductance
- Very small reverse capacitance



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Reverse voltage	V _R	50	V
Forward current	I _F	100	mA
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C
Junction soldering point	R _{thJS}	100	K/W

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse voltage	V _R	I _R = 10 μA	50			V
Reverse current	I _R	V _R = 35 V			10	nA
Forward voltage	V _F	I _F = 100 mA			1.2	V
Diode capacitance	C _D	f = 1 MHz, V _R = 0		0.28		pF
	C _D	f = 1 MHz, V _R = 5 V		0.23	0.3	
Forward resistance	r _f	f = 100 MHz, I _F = 1 mA		2.0		Ω
		f = 100 MHz, I _F = 5 mA		1.1	2.0	
		f = 100 MHz, I _F = 10 mA		0.9		
Charge carrier life time	t _{rr}	I _F = 10 mA, I _R = 6 mA, i _R = 3 mA		115		ns

■ Marking

Marking	C
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